

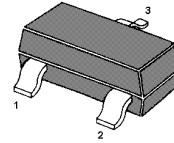
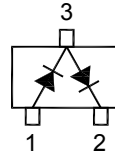
MMBD350SE

Silicon Epitaxial Planar Switching Diode

High Voltage Switching Diode

Features

- Fast switching speed
- High Conductance
- High Reverse Breakdown Voltage Rating



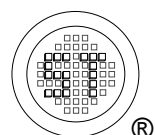
Marking Code: "PY"
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	350	V
Working Peak Reverse Voltage	V_{RWM}	300	V
DC Blocking Voltage	V_R	300	V
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	1	A
		4	
at $t = 1\text{ s}$ at $t = 1\text{ }\mu\text{s}$			
Power Dissipation	P_d	350	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	350	-	V
Forward Voltage at $I_F = 20\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	-	0.87	V
		-	1	
		-	1.25	
Reverse Current at $V_R = 240\text{ V}$ at $V_R = 240\text{ V}, T_j = 150^\circ\text{C}$	I_R	-	100	nA
		-	100	μA
Total Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_T	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}$, $I_{rr} = 0.1 I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	50	ns



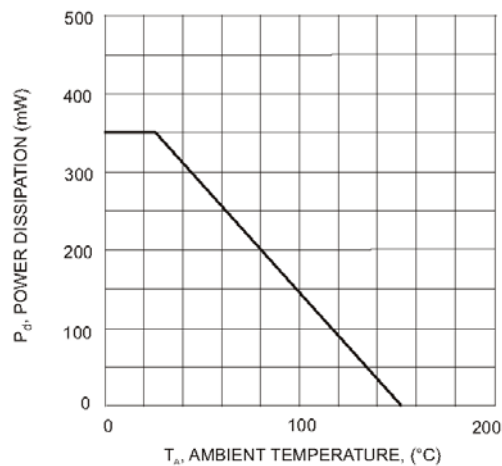


Fig. 1 Power Derating Curve, total package

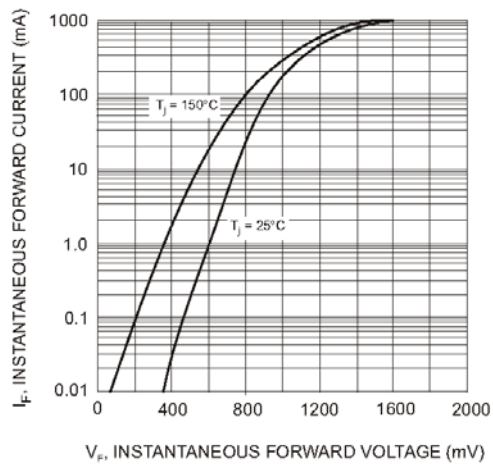


Fig. 2 Typical Forward Characteristics, per element

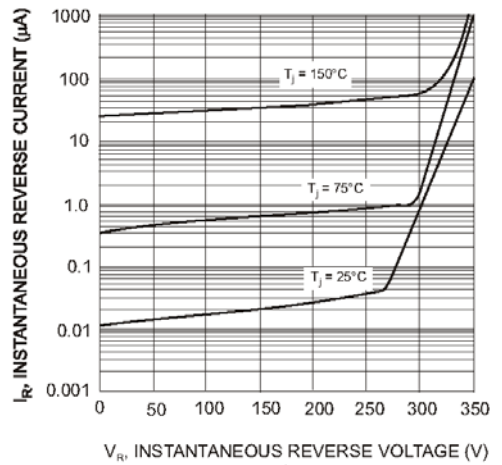


Fig. 3 Typical Reverse Characteristics, per element

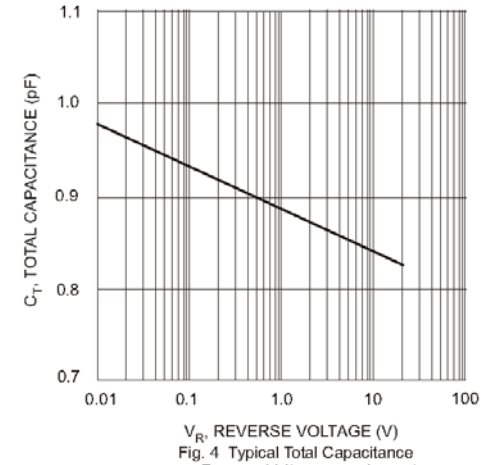


Fig. 4 Typical Total Capacitance vs. Reverse Voltage, per element

